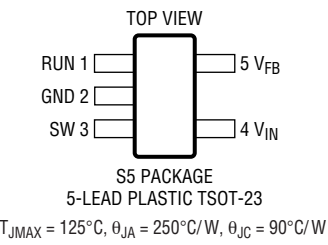
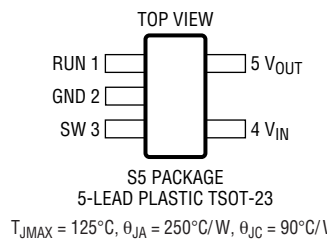


ABSOLUTE MAXIMUM RATINGS (Note 1)

Input Supply Voltage	–0.3V to 6V	Peak SW Sink and Source Current	1.3A
RUN, V_{FB} Voltages	–0.3V to V_{IN}	Operating Temperature Range (Note 2) ..	–40°C to 85°C
SW Voltage	–0.3V to ($V_{IN} + 0.3V$)	Junction Temperature (Notes 3, 6)	125°C
P-Channel Switch Source Current (DC)	800mA	Storage Temperature Range	–65°C to 150°C
N-Channel Switch Sink Current (DC)	800mA	Lead Temperature (Soldering, 10 sec)	300°C

PACKAGE/ORDER INFORMATION

	ORDER PART NUMBER		ORDER PART NUMBER
	LTC3406BES5		LTC3406BES5-1.5 LTC3406BES5-1.8
	S5 PART MARKING		S5 PART MARKING
	LTE2		LTE3 LTE4

Consult LTC Marketing for parts specified with wider operating temperature ranges.

ELECTRICAL CHARACTERISTICS The ● denotes specifications which apply over the full operating temperature range, otherwise specifications are $T_A = 25^\circ\text{C}$. $V_{IN} = 3.6V$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
I _{VFB}	Feedback Current		●			±30	nA
V _{FB}	Regulated Feedback Voltage	LTC3406B (Note 4) T _A = 25°C LTC3406B (Note 4) 0°C ≤ T _A ≤ 85°C LTC3406B (Note 4) −40°C ≤ T _A ≤ 85°C	●	0.5880 0.5865 0.5850	0.6 0.6 0.6	0.6120 0.6135 0.6150	V V V
ΔV _{FB}	Reference Voltage Line Regulation	V _{IN} = 2.5V to 5.5V (Note 4)	●		0.04	0.4	%/V
V _{OUT}	Regulated Output Voltage	LTC3406B-1.5 LTC3406B-1.8	● ●	1.455 1.746	1.500 1.800	1.545 1.854	V V
ΔV _{OVL}	Output Overvoltage Lockout	ΔV _{OVL} = V _{OVL} − V _{FB} , LTC3406B ΔV _{OVL} = V _{OVL} − V _{OUT} , LTC3406B-1.5/LTC3406B-1.8		20 2.5	50 7.8	80 13	mV %
ΔV _{OUT}	Output Voltage Line Regulation	V _{IN} = 2.5V to 5.5V	●		0.04	0.4	%
I _{PK}	Peak Inductor Current	V _{IN} = 3V, V _{FB} = 0.5V or V _{OUT} = 90%, Duty Cycle < 35%		0.75	1	1.25	A
V _{LOADREG}	Output Voltage Load Regulation				0.5		%/V
V _{IN}	Input Voltage Range		●	2.5		5.5	V
I _S	Input DC Bias Current	(Note 5) V _{FB} = 0.5V or V _{OUT} = 90%			300	400	μA
	Shutdown	V _{RUN} = 0V, V _{IN} = 4.2V			0.1	1	μA
f _{OSC}	Oscillator Frequency	V _{FB} = 0.6V or V _{OUT} = 100% V _{FB} = 0V or V _{OUT} = 0V	●	1.2	1.5 210	1.8	MHz kHz
R _{PFET}	R _{DS(ON)} of P-Channel FET	I _{SW} = 100mA			0.4	0.5	Ω
R _{NFET}	R _{DS(ON)} of N-Channel FET	I _{SW} = −100mA			0.35	0.45	Ω
I _{LSW}	SW Leakage	V _{RUN} = 0V, V _{SW} = 0V or 5V, V _{IN} = 5V			±0.01	±1	μA

3406bfa

ELECTRICAL CHARACTERISTICS

The ● denotes specifications which apply over the full operating temperature range, otherwise specifications are $T_A = 25^\circ\text{C}$. $V_{IN} = 3.6\text{V}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
V_{RUN}	RUN Threshold	●	0.3	1	1.5	V
I_{RUN}	RUN Leakage Current	●		± 0.01	± 1	μA

Note 1: Absolute Maximum Ratings are those values beyond which the life of a device may be impaired.

Note 2: The LTC3406BE is guaranteed to meet performance specifications from 0°C to 70°C . Specifications over the -40°C to 85°C operating temperature range are assured by design, characterization and correlation with statistical process controls.

Note 3: T_J is calculated from the ambient temperature T_A and power dissipation P_D according to the following formula:

$$T_J = T_A + (P_D)(250^\circ\text{C}/\text{W})$$

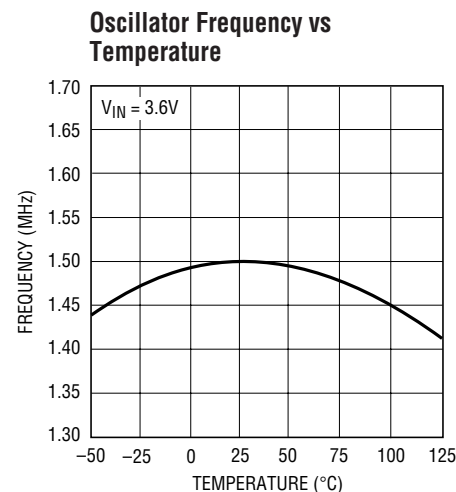
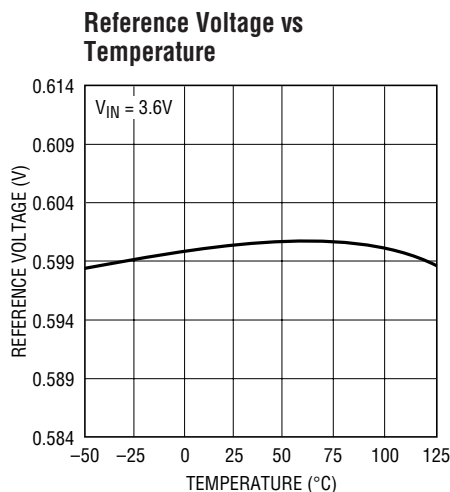
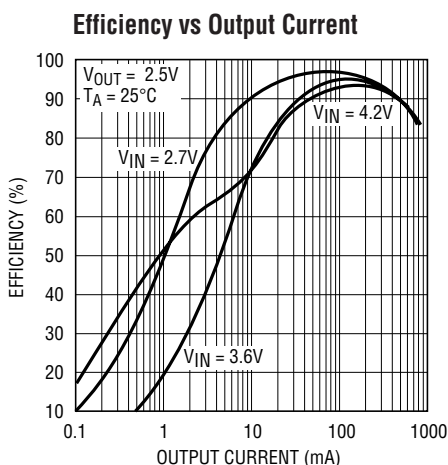
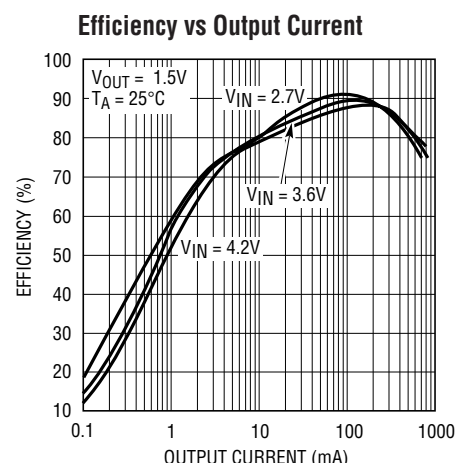
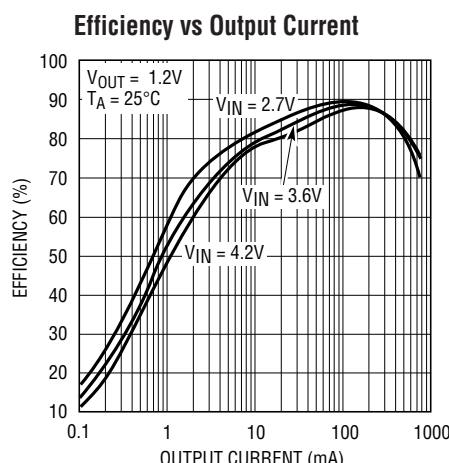
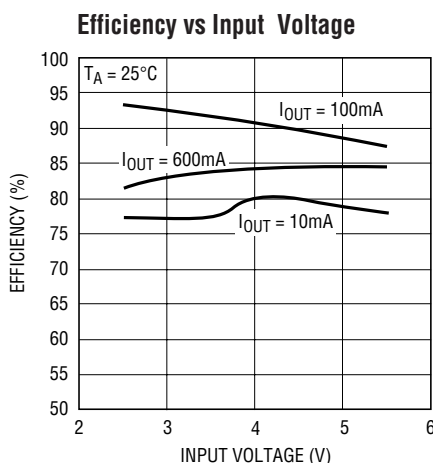
Note 4: The LTC3406B is tested in a proprietary test mode that connects V_{FB} to the output of the error amplifier.

Note 5: Dynamic supply current is higher due to the gate charge being delivered at the switching frequency.

Note 6: This IC includes overtemperature protection that is intended to protect the device during momentary overload conditions. Junction temperature will exceed 125°C when overtemperature protection is active. Continuous operation above the specified maximum operating junction temperature may impair device reliability.

TYPICAL PERFORMANCE CHARACTERISTICS

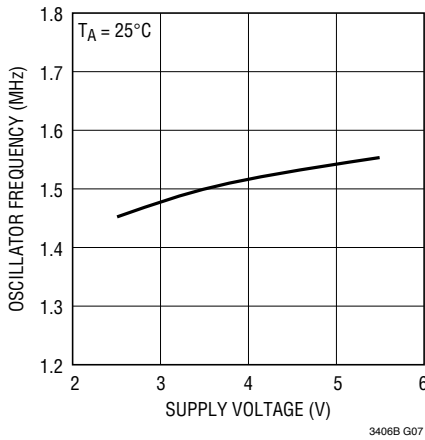
(From Figure 1a Except for the Resistive Divider Resistor Values)



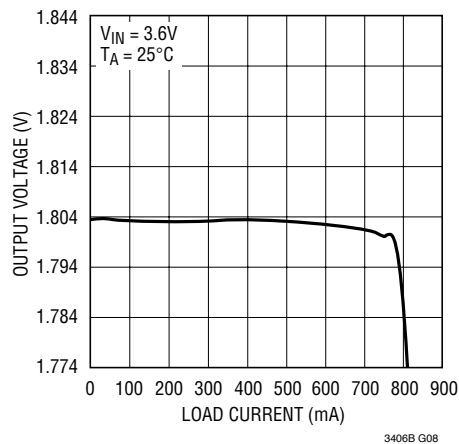
TYPICAL PERFORMANCE CHARACTERISTICS

(From Figure1a Except for the Resistive Divider Resistor Values)

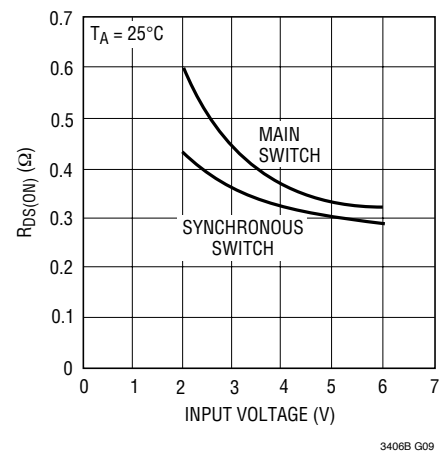
Oscillator Frequency vs Supply Voltage



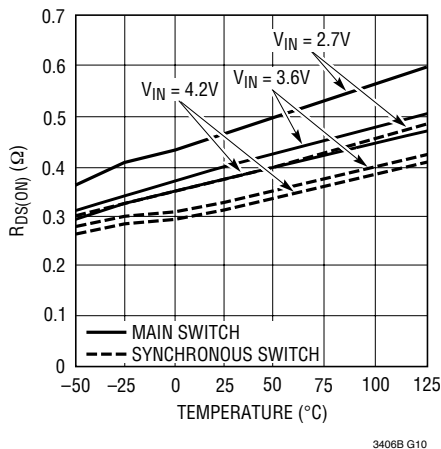
Output Voltage vs Load Current



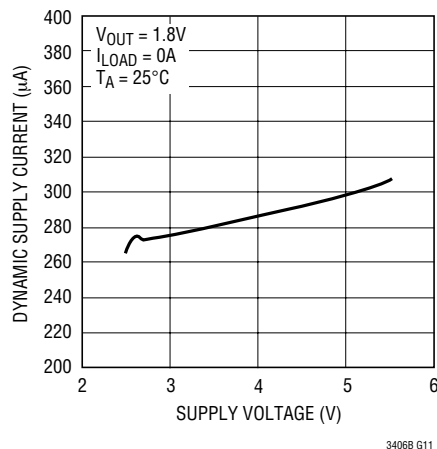
$R_{DS(ON)}$ vs Input Voltage



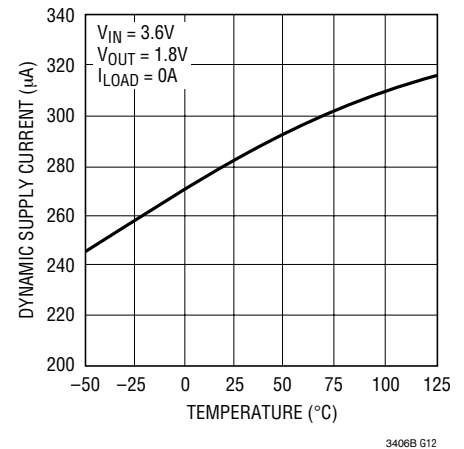
$R_{DS(ON)}$ vs Temperature



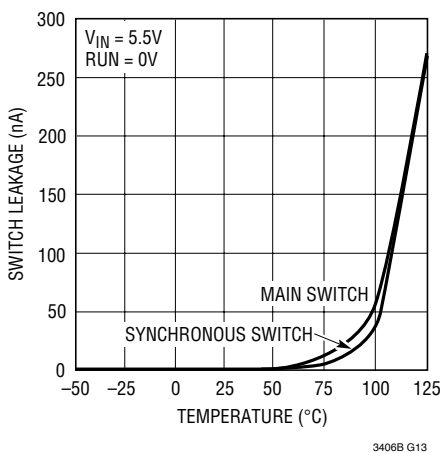
Dynamic Supply Current vs Supply Voltage



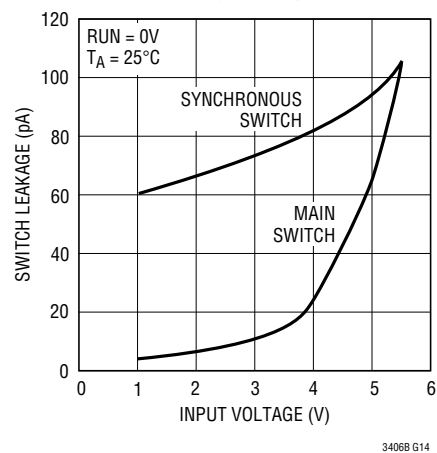
Dynamic Supply Current vs Temperature



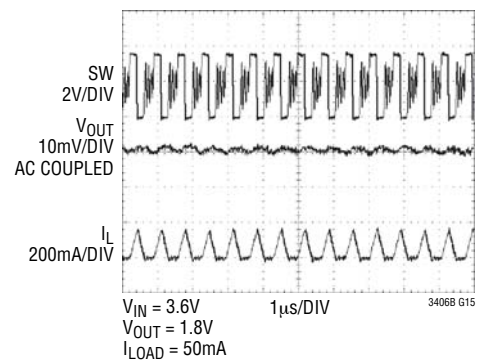
Switch Leakage vs Temperature



Switch Leakage vs Input Voltage

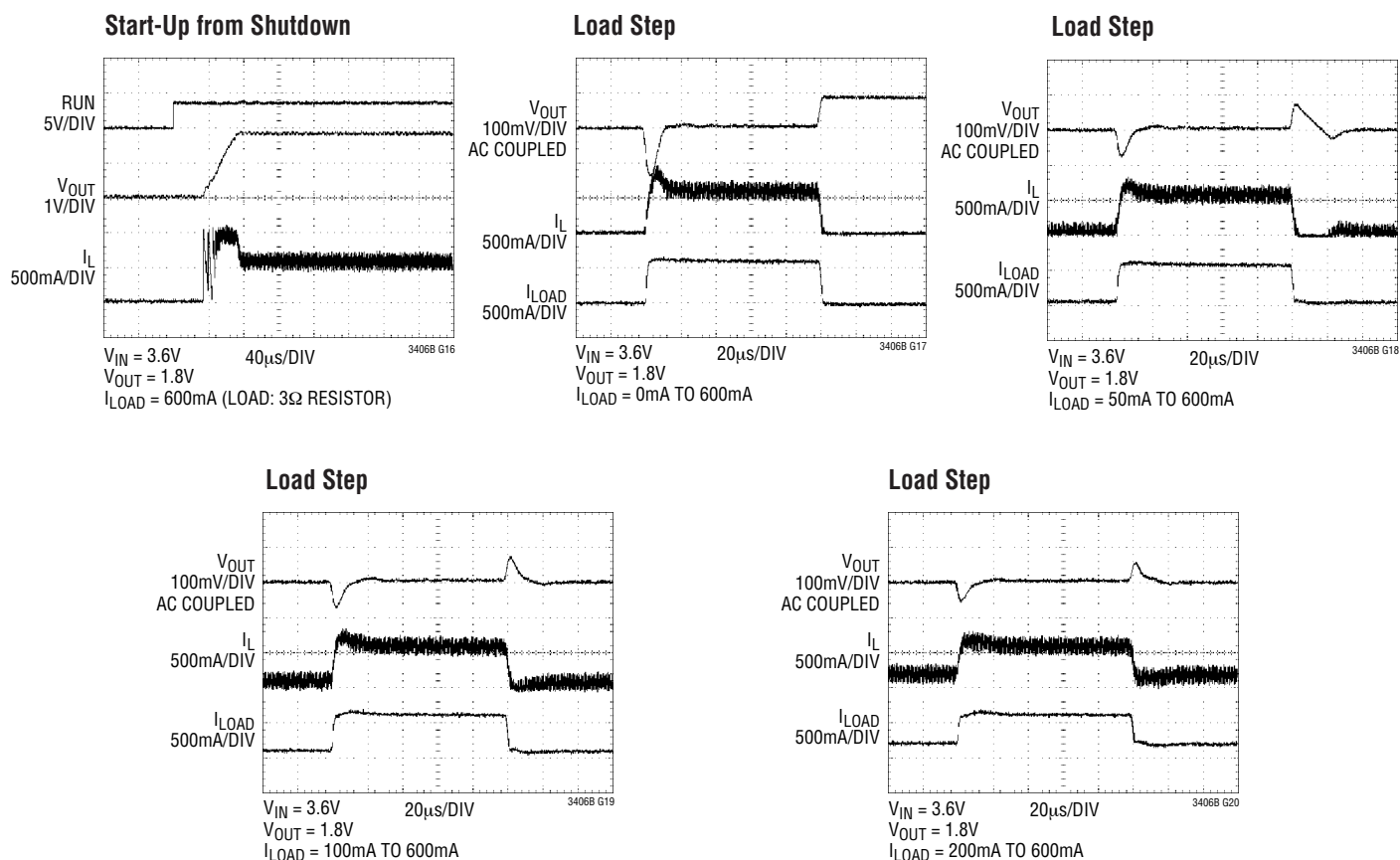


Discontinuous Operation



TYPICAL PERFORMANCE CHARACTERISTICS

(From Figure 1a Except for the Resistive Divider Resistor Values)



PIN FUNCTIONS

RUN (Pin 1): Run Control Input. Forcing this pin above 1.5V enables the part. Forcing this pin below 0.3V shuts down the device. In shutdown, all functions are disabled drawing $<1\mu A$ supply current. Do not leave RUN floating.

GND (Pin 2): Ground Pin.

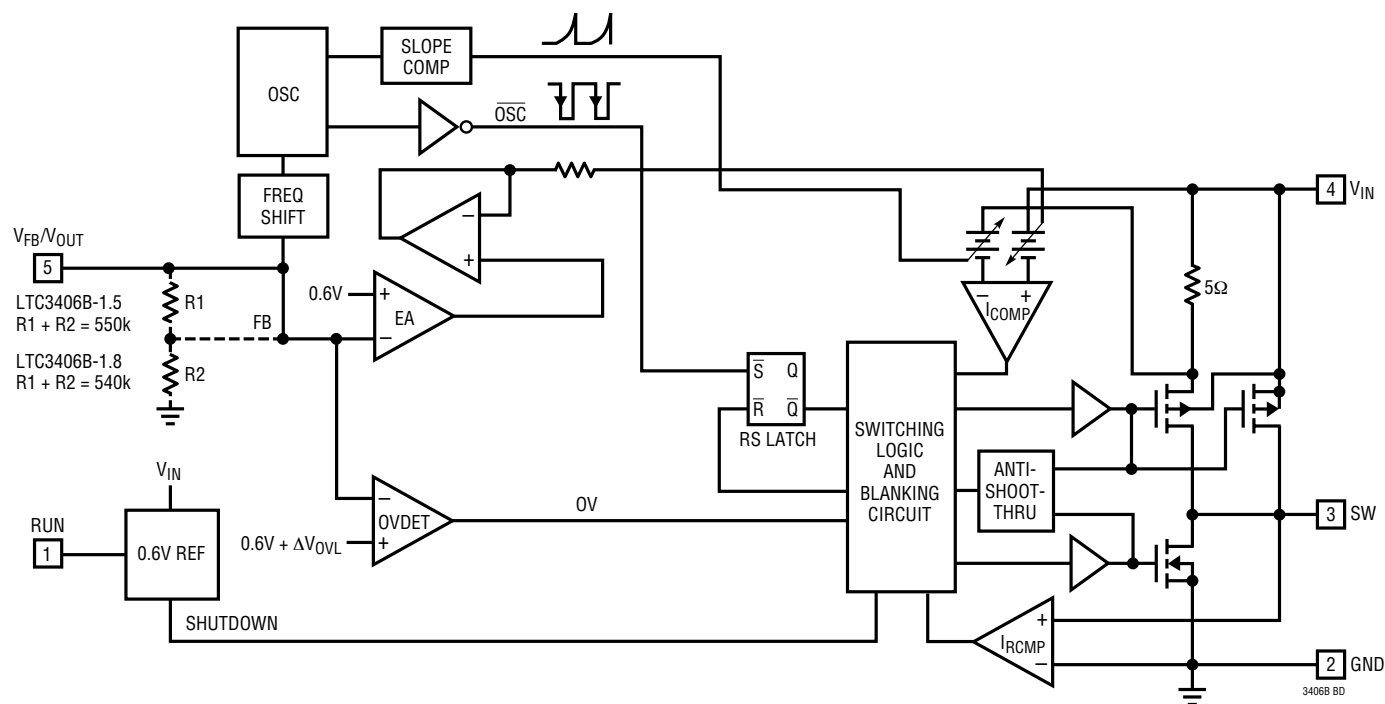
SW (Pin 3): Switch Node Connection to Inductor. This pin connects to the drains of the internal main and synchronous power MOSFET switches.

V_{IN} (Pin 4): Main Supply Pin. Must be closely decoupled to GND, Pin 2, with a 2.2 μF or greater ceramic capacitor.

V_{FB} (Pin 5) (LTC3406B): Feedback Pin. Receives the feedback voltage from an external resistive divider across the output.

V_{OUT} (Pin 5) (LTC3406B-1.5/LTC3406B-1.8): Output Voltage Feedback Pin. An internal resistive divider divides the output voltage down for comparison to the internal reference voltage.

FUNCTIONAL DIAGRAM



OPERATION (Refer to Functional Diagram)

Main Control Loop

The LTC3406B uses a constant frequency, current mode step-down architecture. Both the main (P-channel MOSFET) and synchronous (N-channel MOSFET) switches are internal. During normal operation, the internal top power MOSFET is turned on each cycle when the oscillator sets the RS latch, and turned off when the current comparator, I_{COMP} , resets the RS latch. The peak inductor current at which I_{COMP} resets the RS latch, is controlled by the output of error amplifier EA. When the load current increases, it causes a slight decrease in the feedback voltage, FB, relative to the 0.6V reference, which in turn, causes the EA amplifier's output voltage to increase until the average inductor current matches the new load current. While the top MOSFET is off, the bottom MOSFET is turned on until either the inductor current starts to reverse, as indicated by the current reversal comparator I_{RCMP} , or the beginning of the next clock cycle. The comparator OVDET guards against transient overshoots $>7.8\%$ by turning the main switch off and keeping it off until the fault is removed.

Pulse Skipping Mode Operation

At light loads, the inductor current may reach zero or reverse on each pulse. The bottom MOSFET is turned off by the current reversal comparator, I_{RCMP} , and the switch voltage will ring. This is discontinuous mode operation, and is normal behavior for the switching regulator. At very light loads, the LTC3406B will automatically skip pulses in pulse skipping mode operation to maintain output regulation. Refer to LTC3406 data sheet if Burst Mode operation is preferred.

Short-Circuit Protection

When the output is shorted to ground, the frequency of the oscillator is reduced to about 210kHz, 1/7 the nominal frequency. This frequency foldback ensures that the inductor current has more time to decay, thereby preventing runaway. The oscillator's frequency will progressively increase to 1.5MHz when V_{FB} or V_{OUT} rises above 0V.

OPERATION (Refer to Functional Diagram)

Dropout Operation

As the input supply voltage decreases to a value approaching the output voltage, the duty cycle increases toward the maximum on-time. Further reduction of the supply voltage forces the main switch to remain on for more than one cycle until it reaches 100% duty cycle. The output voltage will then be determined by the input voltage minus the voltage drop across the P-channel MOSFET and the inductor.

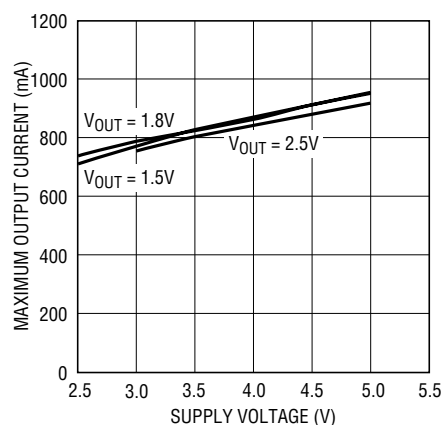
An important detail to remember is that at low input supply voltages, the $R_{DS(ON)}$ of the P-channel switch increases (see Typical Performance Characteristics). Therefore, the user should calculate the power dissipation when the LTC3406B is used at 100% duty cycle with low input voltage (See Thermal Considerations in the Applications Information section).

Low Supply Operation

The LTC3406B will operate with input supply voltages as low as 2.5V, but the maximum allowable output current is reduced at this low voltage. Figure 2 shows the reduction in the maximum output current as a function of input voltage for various output voltages.

Slope Compensation and Inductor Peak Current

Slope compensation provides stability in constant frequency architectures by preventing subharmonic oscillations at high duty cycles. It is accomplished internally by adding a compensating ramp to the inductor current signal at duty cycles in excess of 40%. Normally, this results in a reduction of maximum inductor peak current for duty cycles $>40\%$. However, the LTC3406B uses a patent-pending scheme that counteracts this compensating ramp, which allows the maximum inductor peak current to remain unaffected throughout all duty cycles.



3406B F02

Figure 2. Maximum Output Current vs Input Voltage

APPLICATIONS INFORMATION

The basic LTC3406B application circuit is shown in Figure 1. External component selection is driven by the load requirement and begins with the selection of L followed by C_{IN} and C_{OUT} .

Inductor Selection

For most applications, the value of the inductor will fall in the range of 1 μ H to 4.7 μ H. Its value is chosen based on the desired ripple current. Large value inductors lower ripple current and small value inductors result in higher ripple currents. Higher V_{IN} or V_{OUT} also increases the ripple current as shown in equation 1. A reasonable starting point for setting ripple current is $\Delta I_L = 240\text{mA}$ (40% of 600mA).

$$\Delta I_L = \frac{1}{(f)(L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right) \quad (1)$$

The DC current rating of the inductor should be at least equal to the maximum load current plus half the ripple current to prevent core saturation. Thus, a 720mA rated inductor should be enough for most applications (600mA + 120mA). For better efficiency, choose a low DC-resistance inductor.

Inductor Core Selection

Different core materials and shapes will change the size/current and price/current relationship of an inductor. Toroid or shielded pot cores in ferrite or permalloy materials are small and don't radiate much energy, but generally cost more than powdered iron core inductors with similar electrical characteristics. The choice of which style inductor to use often depends more on the price vs size requirements and any radiated field/EMI requirements than on what the LTC3406B requires to operate. Table 1 shows some typical surface mount inductors that work well in LTC3406B applications.

Table 1. Representative Surface Mount Inductors

PART NUMBER	VALUE (μ H)	DCR (Ω MAX)	MAX DC CURRENT (A)	SIZE W $\times$ L $\times$ H (mm ³)
Sumida CDRH3D16	1.5	0.043	1.55	3.8 $\times$ 3.8 $\times$ 1.8
	2.2	0.075	1.20	
	3.3	0.110	1.10	
	4.7	0.162	0.90	
Sumida CMD4D06	2.2	0.116	0.950	3.5 $\times$ 4.3 $\times$ 0.8
	3.3	0.174	0.770	
	4.7	0.216	0.750	
Panasonic ELT5KT	3.3	0.17	1.00	4.5 $\times$ 5.4 $\times$ 1.2
	4.7	0.20	0.95	
Murata LQH3C	1.0	0.060	1.00	2.5 $\times$ 3.2 $\times$ 2.0
	2.2	0.097	0.79	
	4.7	0.150	0.65	

C_{IN} and C_{OUT} Selection

In continuous mode, the source current of the top MOSFET is a square wave of duty cycle V_{OUT}/V_{IN} . To prevent large voltage transients, a low ESR input capacitor sized for the maximum RMS current must be used. The maximum RMS capacitor current is given by:

$$C_{IN} \text{ required } I_{RMS} \approx I_{OMAX} \frac{\left[V_{OUT}(V_{IN} - V_{OUT}) \right]^{1/2}}{V_{IN}}$$

This formula has a maximum at $V_{IN} = 2V_{OUT}$, where $I_{RMS} = I_{OUT}/2$. This simple worst-case condition is commonly used for design because even significant deviations do not offer much relief. Note that the capacitor manufacturer's ripple current ratings are often based on 2000 hours of life. This makes it advisable to further derate the capacitor, or choose a capacitor rated at a higher temperature than required. Always consult the manufacturer if there is any question.

The selection of C_{OUT} is driven by the required effective series resistance (ESR).

APPLICATIONS INFORMATION

Typically, once the ESR requirement for C_{OUT} has been met, the RMS current rating generally far exceeds the $I_{RIPPLE(P-P)}$ requirement. The output ripple ΔV_{OUT} is determined by:

$$\Delta V_{OUT} \approx \Delta I_L \left(ESR + \frac{1}{8fC_{OUT}} \right)$$

where f = operating frequency, C_{OUT} = output capacitance and ΔI_L = ripple current in the inductor. For a fixed output voltage, the output ripple is highest at maximum input voltage since ΔI_L increases with input voltage.

Aluminum electrolytic and dry tantalum capacitors are both available in surface mount configurations. In the case of tantalum, it is critical that the capacitors are surge tested for use in switching power supplies. An excellent choice is the AVX TPS series of surface mount tantalum. These are specially constructed and tested for low ESR so they give the lowest ESR for a given volume. Other capacitor types include Sanyo POSCAP, Kemet T510 and T495 series, and Sprague 593D and 595D series. Consult the manufacturer for other specific recommendations.

Using Ceramic Input and Output Capacitors

Higher values, lower cost ceramic capacitors are now becoming available in smaller case sizes. Their high ripple current, high voltage rating and low ESR make them ideal for switching regulator applications. Because the LTC3406B's control loop does not depend on the output capacitor's ESR for stable operation, ceramic capacitors can be used **freely** to achieve very low output ripple and small circuit size.

However, care must be taken when ceramic capacitors are used at the input and the output. When a ceramic capacitor is used at the input and the power is supplied by a wall adapter through long wires, a load step at the output can induce ringing at the input, V_{IN} . At best, this ringing can

couple to the output and be mistaken as loop instability. At worst, a sudden inrush of current through the long wires can potentially cause a voltage spike at V_{IN} , large enough to damage the part.

When choosing the input and output ceramic capacitors, choose the X5R or X7R dielectric formulations. These dielectrics have the best temperature and voltage characteristics of all the ceramics for a given value and size.

Output Voltage Programming (LTC3406B Only)

In the adjustable version, the output voltage is set by a resistive divider according to the following formula:

$$V_{OUT} = 0.6V \left(1 + \frac{R2}{R1} \right) \quad (2)$$

The external resistive divider is connected to the output, allowing remote voltage sensing as shown in Figure 3.

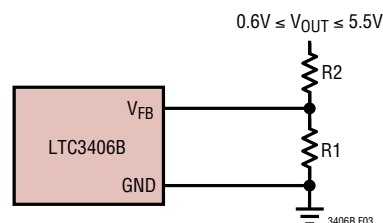


Figure 3. Setting the LTC3406B Output Voltage

Efficiency Considerations

The efficiency of a switching regulator is equal to the output power divided by the input power times 100%. It is often useful to analyze individual losses to determine what is limiting the efficiency and which change would produce the most improvement. Efficiency can be expressed as:

$$\text{Efficiency} = 100\% - (L1 + L2 + L3 + \dots)$$

where $L1$, $L2$, etc. are the individual losses as a percentage of input power.

APPLICATIONS INFORMATION

Although all dissipative elements in the circuit produce losses, two main sources usually account for most of the losses in LTC3406B circuits: V_{IN} quiescent current and I^2R losses. The V_{IN} quiescent current loss dominates the efficiency loss at very low load currents whereas the I^2R loss dominates the efficiency loss at medium to high load currents. In a typical efficiency plot, the efficiency curve at very low load currents can be misleading since the actual power lost is of no consequence as illustrated in Figure 4.

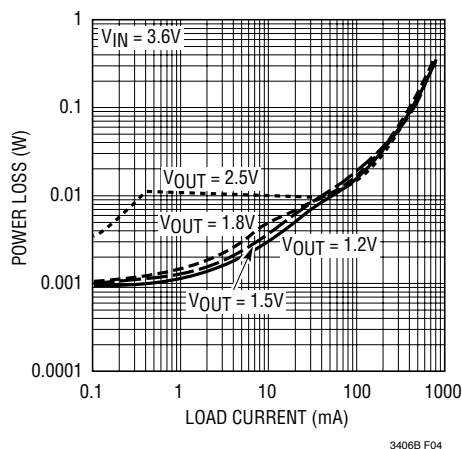


Figure 4. Power Lost vs Load Current

1. The V_{IN} quiescent current is due to two components: the DC bias current as given in the electrical characteristics and the internal main switch and synchronous switch gate charge currents. The gate charge current results from switching the gate capacitance of the internal power MOSFET switches. Each time the gate is switched from high to low to high again, a packet of charge, dQ , moves from V_{IN} to ground. The resulting dQ/dt is the current out of V_{IN} that is typically larger than the DC bias current. In continuous mode, $I_{GATECHG} = f(Q_T + Q_B)$ where Q_T and Q_B are the gate charges of the internal top and bottom switches. Both the DC bias and gate charge losses are proportional to V_{IN} and thus their effects will be more pronounced at higher supply voltages.

2. I^2R losses are calculated from the resistances of the internal switches, R_{SW} , and external inductor R_L . In continuous mode, the average output current flowing through inductor L is “chopped” between the main switch and the synchronous switch. Thus, the series resistance looking into the SW pin is a function of both top and bottom MOSFET $R_{DS(ON)}$ and the duty cycle (DC) as follows:

$$R_{SW} = (R_{DS(ON)TOP})(DC) + (R_{DS(ON)BOT})(1 - DC)$$

The $R_{DS(ON)}$ for both the top and bottom MOSFETs can be obtained from the Typical Performance Characteristics curves. Thus, to obtain I^2R losses, simply add R_{SW} to R_L and multiply the result by the square of the average output current.

Other losses including C_{IN} and C_{OUT} ESR dissipative losses and inductor core losses generally account for less than 2% total additional loss.

Thermal Considerations

In most applications the LTC3406B does not dissipate much heat due to its high efficiency. But, in applications where the LTC3406B is running at high ambient temperature with low supply voltage and high duty cycles, such as in dropout, the heat dissipated may exceed the maximum junction temperature of the part. If the junction temperature reaches approximately 150°C, both power switches will be turned off and the SW node will become high impedance.

To avoid the LTC3406B from exceeding the maximum junction temperature, the user will need to do some thermal analysis. The goal of the thermal analysis is to determine whether the power dissipated exceeds the maximum junction temperature of the part. The temperature rise is given by:

$$T_R = (P_D)(\theta_{JA})$$

where P_D is the power dissipated by the regulator and θ_{JA} is the thermal resistance from the junction of the die to the ambient temperature.

APPLICATIONS INFORMATION

The junction temperature, T_J , is given by:

$$T_J = T_A + T_R$$

where T_A is the ambient temperature.

As an example, consider the LTC3406B in dropout at an input voltage of 2.7V, a load current of 600mA and an ambient temperature of 70°C. From the typical performance graph of switch resistance, the $R_{DS(ON)}$ of the P-channel switch at 70°C is approximately 0.52Ω. Therefore, power dissipated by the part is:

$$P_D = I_{LOAD}^2 \cdot R_{DS(ON)} = 187.2\text{mW}$$

For the SOT-23 package, the θ_{JA} is 250°C/W. Thus, the junction temperature of the regulator is:

$$T_J = 70^\circ\text{C} + (0.1872)(250) = 116.8^\circ\text{C}$$

which is below the maximum junction temperature of 125°C.

Note that at higher supply voltages, the junction temperature is lower due to reduced switch resistance ($R_{DS(ON)}$).

Checking Transient Response

The regulator loop response can be checked by looking at the load transient response. Switching regulators take several cycles to respond to a step in load current. When a load step occurs, V_{OUT} immediately shifts by an amount equal to $(\Delta I_{LOAD} \cdot ESR)$, where ESR is the effective series resistance of C_{OUT} . ΔI_{LOAD} also begins to charge or discharge C_{OUT} , which generates a feedback error signal. The regulator loop then acts to return V_{OUT} to its steady-state value. During this recovery time V_{OUT} can be monitored for overshoot or ringing that would indicate a stability problem. For a detailed explanation of switching control loop theory, see Application Note 76.

A second, more severe transient is caused by switching in loads with large ($>1\mu\text{F}$) supply bypass capacitors. The discharged bypass capacitors are effectively put in parallel with C_{OUT} , causing a rapid drop in V_{OUT} . No regulator can deliver enough current to prevent this problem if the load switch resistance is low and it is driven quickly. The only solution is to limit the rise time of the switch drive so that the load rise time is limited to approximately $(25 \cdot C_{LOAD})$. Thus, a 10μF capacitor charging to 3.3V would require a 250μs rise time, limiting the charging current to about 130mA.

PC Board Layout Checklist

When laying out the printed circuit board, the following checklist should be used to ensure proper operation of the LTC3406B. These items are also illustrated graphically in Figures 5 and 6. Check the following in your layout:

1. The power traces, consisting of the GND trace, the SW trace and the V_{IN} trace should be kept short, direct and wide.
2. Does the V_{FB} pin connect directly to the feedback resistors? The resistive divider R1/R2 must be connected between the (+) plate of C_{OUT} and ground.
3. Does the (+) plate of C_{IN} connect to V_{IN} as closely as possible? This capacitor provides the AC current to the internal power MOSFETs.
4. Keep the switching node, SW, away from the sensitive V_{FB} node.
5. Keep the (–) plates of C_{IN} and C_{OUT} as close as possible.

APPLICATIONS INFORMATION

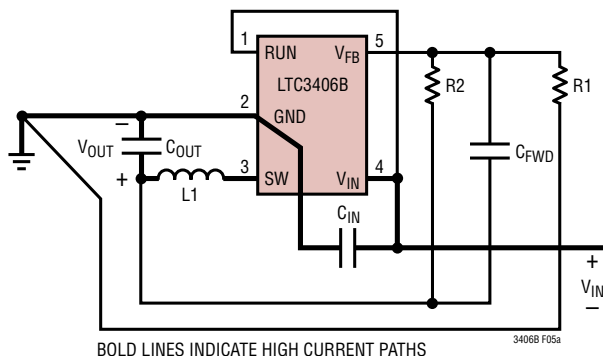


Figure 5a. LTC3406B Layout Diagram

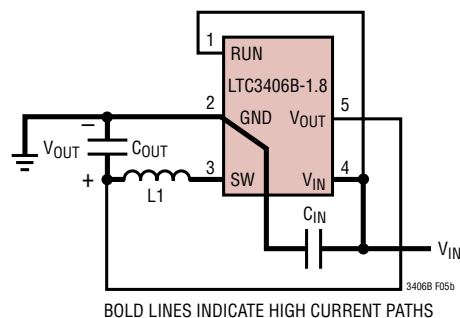


Figure 5b. LTC3406B-1.8 Layout Diagram

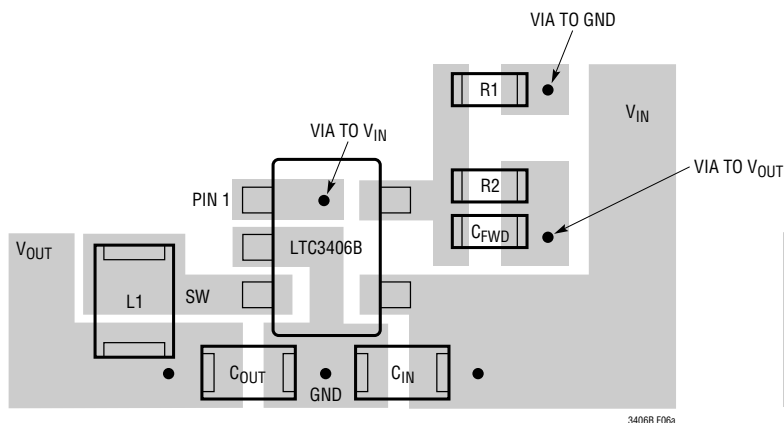


Figure 6a. LTC3406B Suggested Layout

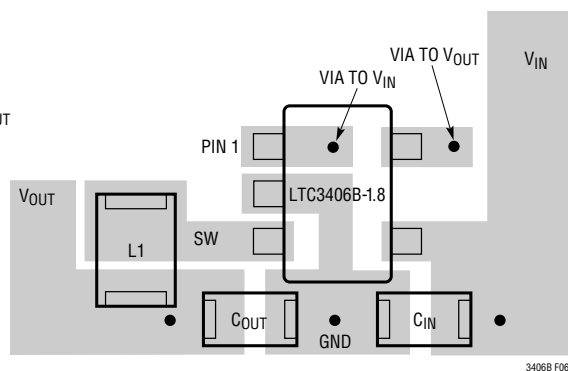


Figure 6b. LTC3406B-1.8 Suggested Layout

Design Example

As a design example, assume the LTC3406B is used in a single lithium-ion battery-powered cellular phone application. The V_{IN} will be operating from a maximum of 4.2V down to about 2.7V. The load current requirement is a maximum of 0.6A but most of the time it will be in standby mode, requiring only 2mA. Efficiency at both low and high load currents is important. Output voltage is 2.5V. With this information we can calculate L using equation (1),

$$L = \frac{1}{f(\Delta I_L)} V_{OUT} \left(1 - \frac{V_{OUT}}{V_{IN}} \right) \quad (3)$$

Substituting $V_{OUT} = 2.5V$, $V_{IN} = 4.2V$, $\Delta I_L = 240mA$ and $f = 1.5MHz$ in equation (3) gives:

$$L = \frac{2.5V}{1.5MHz(240mA)} \left(1 - \frac{2.5V}{4.2V} \right) = 2.81\mu H$$

A 2.2 μH inductor works well for this application. For best efficiency choose a 720mA or greater inductor with less than 0.2 Ω series resistance.

C_{IN} will require an RMS current rating of at least $0.3A \approx I_{LOAD(MAX)}/2$ at temperature and C_{OUT} will require an ESR of less than 0.25 Ω . In most cases, a ceramic capacitor will satisfy this requirement.

APPLICATIONS INFORMATION

For the feedback resistors, choose $R1 = 316k$. $R2$ can then be calculated from equation (2) to be:

$$R2 = \left(\frac{V_{OUT}}{0.6} - 1 \right) R1 = 1000k$$

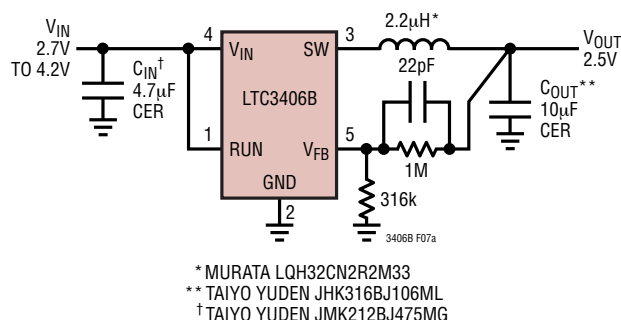


Figure 7a

Figure 7 shows the complete circuit along with its efficiency curve.

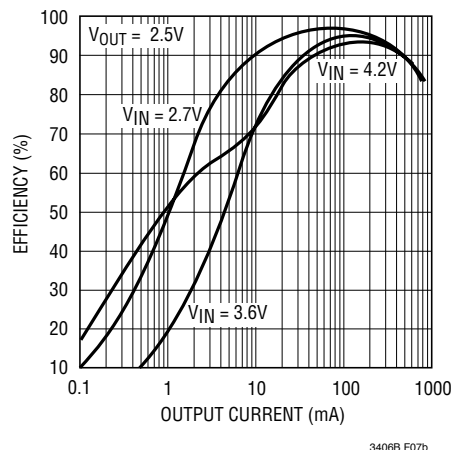
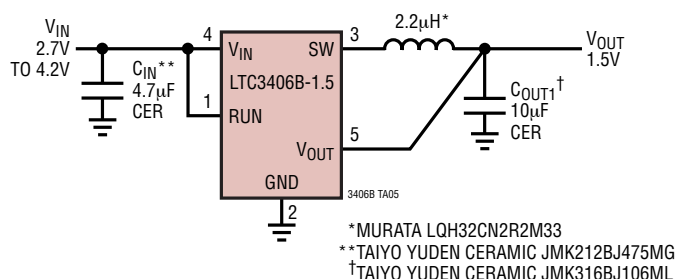


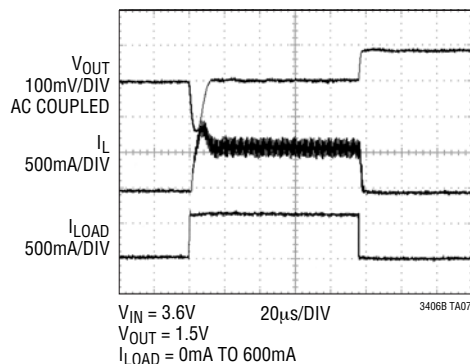
Figure 7b

TYPICAL APPLICATIONS

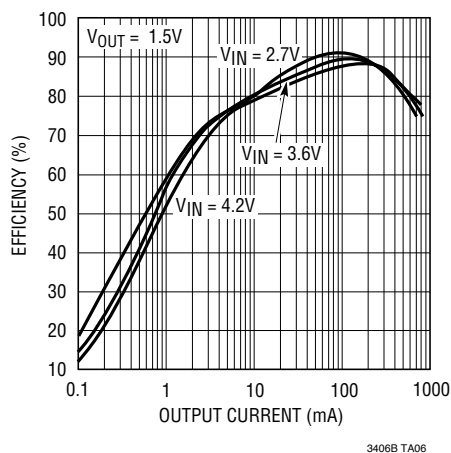
Single Li-Ion 1.5V/600mA Regulator for High Efficiency and Small Footprint



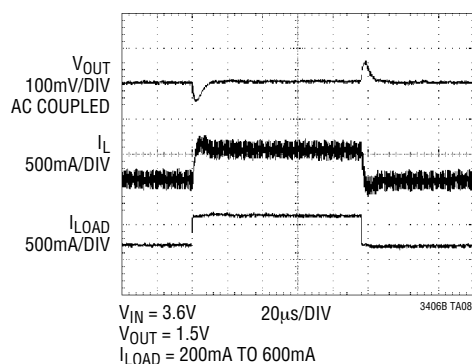
Load Step



Efficiency vs Output Current

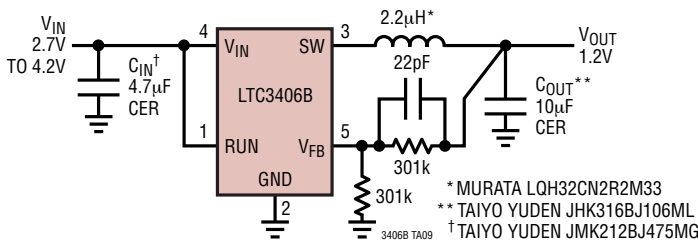


Load Step

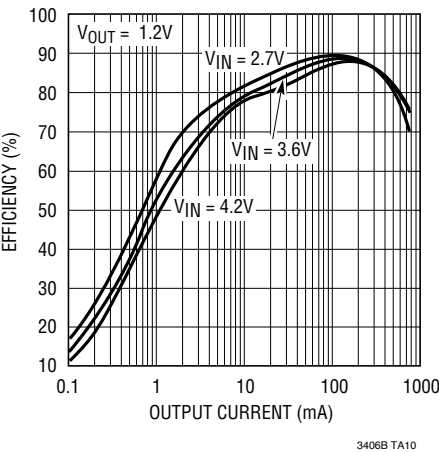


TYPICAL APPLICATIONS

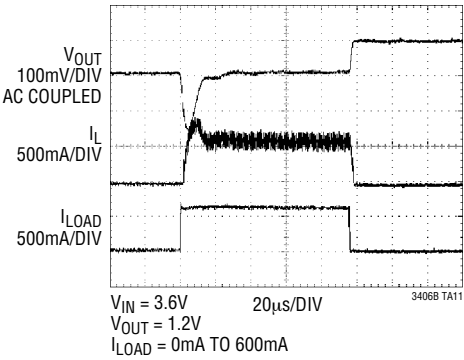
Single Li-Ion 1.2V/600mA Regulator for High Efficiency and Small Footprint



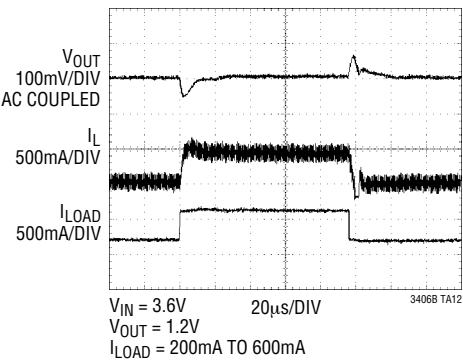
Efficiency vs Output Current



Load Step

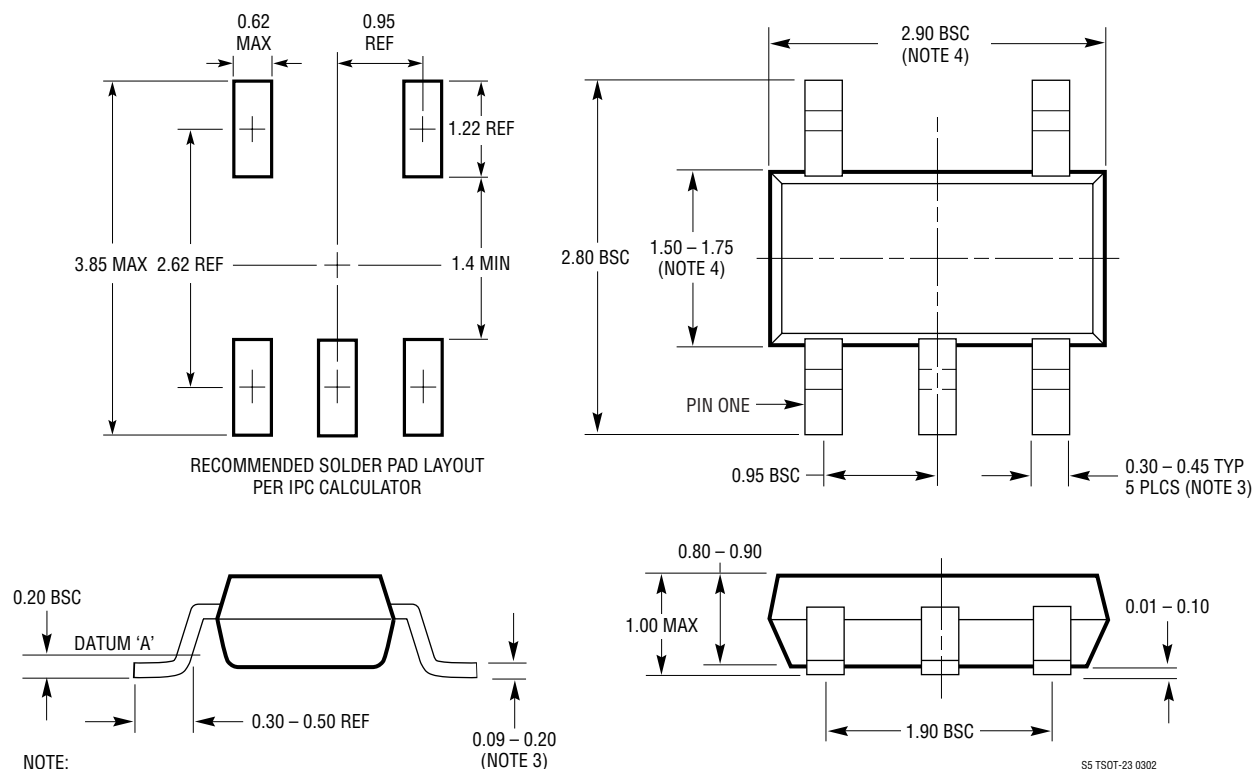


Load Step



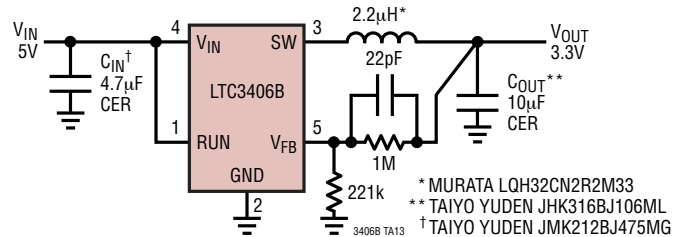
PACKAGE DESCRIPTION

S5 Package
5-Lead Plastic TSOT-23
 (Reference LTC DWG # 05-08-1635)



TYPICAL APPLICATION

5V Input to 3.3V/0.6A Regulator



RELATED PARTS

PART NUMBER	DESCRIPTION	COMMENTS
LT1616	500mA (I_{OUT}), 1.4MHz, High Efficiency Step-Down DC/DC Converter	90% Efficiency, V_{IN} = 3.6V to 25V, V_{OUT} = 1.25V, I_Q = 1.9mA, I_{SD} = <1µA, ThinSOT Package
LT1676	450mA (I_{OUT}), 100kHz, High Efficiency Step-Down DC/DC Converter	90% Efficiency, V_{IN} = 7.4V to 60V, V_{OUT} = 1.24V, I_Q = 3.2mA, I_{SD} = 2.5µA, S8 Package
LTC1701/LT1701B	750mA (I_{OUT}), 1MHz, High Efficiency Step-Down DC/DC Converter	90% Efficiency, V_{IN} = 2.5V to 5V, V_{OUT} = 1.25V, I_Q = 135µA, I_{SD} = <1µA, ThinSOT Package
LT1776	500mA (I_{OUT}), 200kHz, High Efficiency Step-Down DC/DC Converter	90% Efficiency, V_{IN} = 7.4V to 40V, V_{OUT} = 1.24V, I_Q = 3.2mA, I_{SD} = 30µA, N8, S8 Packages
LTC1877	600mA (I_{OUT}), 550kHz, Synchronous Step-Down DC/DC Converter	95% Efficiency, V_{IN} = 2.7V to 10V, V_{OUT} = 0.8V, I_Q = 10µA, I_{SD} = <1µA, MS8 Package
LTC1878	600mA (I_{OUT}), 550kHz, Synchronous Step-Down DC/DC Converter	95% Efficiency, V_{IN} = 2.7V to 6V, V_{OUT} = 0.8V, I_Q = 10µA, I_{SD} = <1µA, MS8 Package
LTC1879	1.2A (I_{OUT}), 550kHz, Synchronous Step-Down DC/DC Converter	95% Efficiency, V_{IN} = 2.7V to 10V, V_{OUT} = 0.8V, I_Q = 15µA, I_{SD} = <1µA, TSSOP-16 Package
LTC3403	600mA (I_{OUT}), 1.5MHz, Synchronous Step-Down DC/DC Converter with Bypass Transistor	96% Efficiency, V_{IN} = 2.5V to 5.5V, V_{OUT} = Dynamically Adjustable, I_Q = 20µA, I_{SD} = <1µA, DFN Package
LTC3404	600mA (I_{OUT}), 1.4MHz, Synchronous Step-Down DC/DC Converter	95% Efficiency, V_{IN} = 2.7V to 6V, V_{OUT} = 0.8V, I_Q = 10µA, I_{SD} = <1µA, MS8 Package
LTC3405/LTC3405A	300mA (I_{OUT}), 1.5MHz, Synchronous Step-Down DC/DC Converter	96% Efficiency, V_{IN} = 2.5V to 5.5V, V_{OUT} = 0.8V, I_Q = 20µA, I_{SD} = <1µA, ThinSOT Package
LTC3406	600mA (I_{OUT}), 1.5MHz, Synchronous Step-Down DC/DC Converter	96% Efficiency, V_{IN} = 2.5V to 5.5V, V_{OUT} = 0.6V, I_Q = 20µA, I_{SD} = <1µA, ThinSOT Package
LTC3411	1.25A (I_{OUT}), 4MHz, Synchronous Step-Down DC/DC Converter	95% Efficiency, V_{IN} = 2.5V to 5.5V, V_{OUT} = 0.8V, I_Q = 60µA, I_{SD} = <1µA, MS Package
LTC3412	2.5A (I_{OUT}), 4MHz, Synchronous Step-Down DC/DC Converter	95% Efficiency, V_{IN} = 2.5V to 5.5V, V_{OUT} = 0.8V, I_Q = 60µA, I_{SD} = <1µA, TSSOP-16E Package
LTC3440	600mA (I_{OUT}), 2MHz, Synchronous Buck-Boost DC/DC Converter	95% Efficiency, V_{IN} = 2.5V to 5.5V, V_{OUT} = 2.5V, I_Q = 25µA, I_{SD} = <1µA, MS Package